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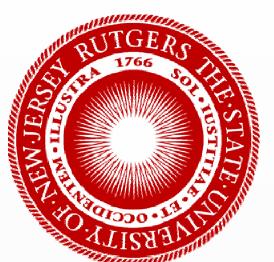
Incoherent transport near the Mott transition

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ABSTRACT

We examine the mechanism for the violation of the Mott-Ioffe-Regel (MIR) condition for the maximal metallic resistivity near the interaction-driven Mott transition. We find that the large resistivity appears due to the large scattering rate which destroys well-defined quasi-particles, while the Drude-like peak in the optical conductivity persists well beyond the MIR limit, similar as in the experiments on VO_2 . The disorder induces effective local carrier doping which moves the system away from the Mott insulator, increasing the conductivity, in agreement with the recent experiments on X-ray irradiated organic charge-transfer salts.

Disordered Hubbard model

$$H = -\sum_{ij,\sigma} t_{i,j} d_{i\sigma}^{\dagger} d_{j\sigma} + U \sum_{i} n_{i\uparrow} n_{i\downarrow} + \varepsilon_{i} \sum_{i\sigma} n_{i\sigma}$$

DMFT approximation

Local Green's function $G_l(au- au)=-\langle Td_\sigma(au)d_\sigma^\dagger(au)
angle_{S_{eff}}$ is obtained form the corresponding Anderson impurity model action [1]

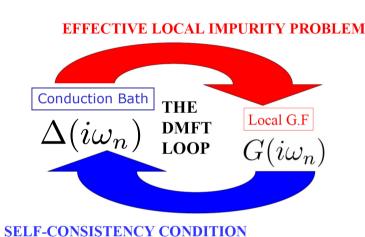
$$S_{eff}^{i} = -\int_{0}^{\beta} d\tau \int_{0}^{\beta} d\tau' \sum_{\sigma} d_{\sigma}^{+}(\tau) \mathcal{G}_{0i}^{-1}(\tau - \tau') d_{\sigma}(\tau') + U \int_{0}^{\beta} d\tau n_{\uparrow}(\tau) n_{\downarrow}(\tau),$$

$$\mathcal{G}_{0i}^{-1}(i\omega_n) = i\omega_n + \mu - \varepsilon_i - \Delta(i\omega_n)$$
 "Weiss field" random site energy conduction bath

Disorder averaging within CPA

$$G(i\omega_n) = \frac{1}{N} \sum_{i=1}^{N} G_i(i\omega_n)$$

DMFT self-consistency loop



$$G(i\omega_n) = \int d\varepsilon \frac{D(\varepsilon)}{\Delta(i\omega_n) + G(i\omega_n)^{-1} - \varepsilon}$$

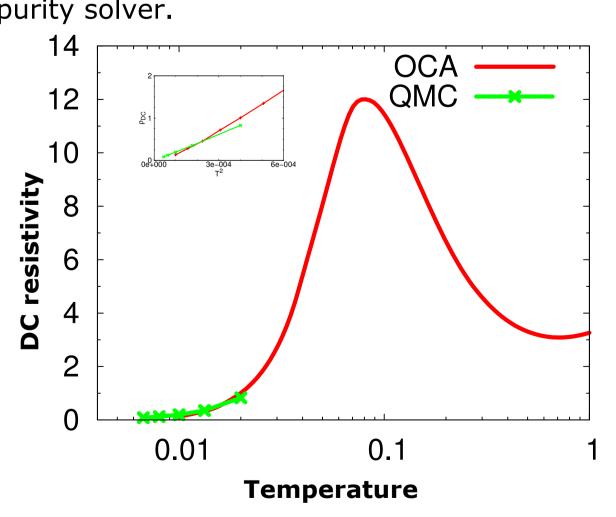
• Kubo formula in DMFT approximation

 $\sigma(i\omega) =$

$$\frac{1}{\omega} \int_{-\infty}^{+\infty} d\epsilon \int_{-\infty}^{+\infty} d\nu \int_{-\infty}^{+\infty} d\nu' D(\epsilon) \rho(\epsilon, \nu) \rho(\epsilon, \nu') \frac{f(\nu) - f(\nu')}{\nu - \nu' + i\omega}$$
 DC resistivity: $\rho_{DC} = \sigma^{-1}(\omega \to 0)$

Impurity solvers

Anderson impurity model is solved using One-Crossing Approximation (OCA) (generalized NCA) [2,3], and the results are cross-checked with numerically exact Continues Time Quantum Monte Carlo (CTQMC) [4] impurity solver.

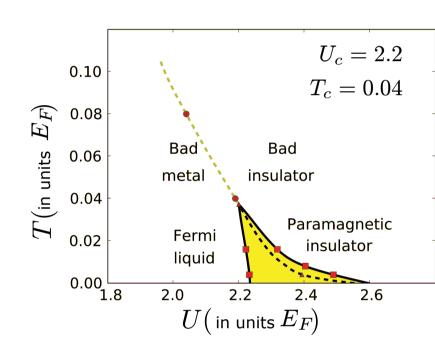


Violation of the MIR condition

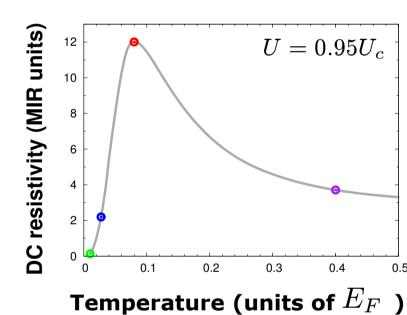
 Mott-Ioffe-Regel limit is the maximal metallic resistivity, ho_{MIR} , which is reached when the mean free path of the electron becomes comparable to the lattice spacing [5] $l \sim a \Leftrightarrow E_F \tau \sim 1.$

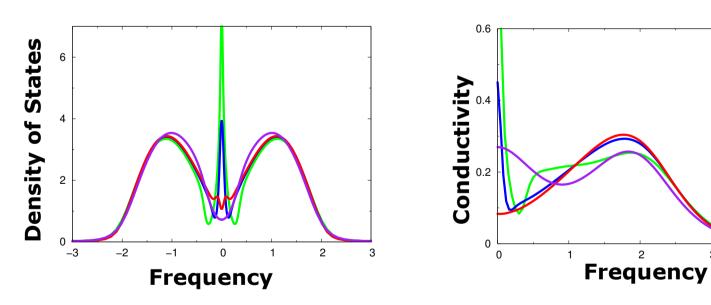
According to semi-classical arguments, resistivity cannot be larger than MIR limit.

Mott metal-insulator transition

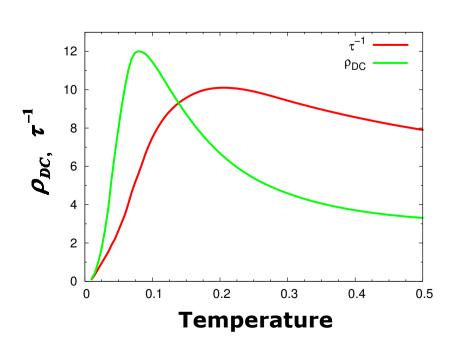


- Results near the critical point
- -Fermi liquid at low temperatures.
- -Drude-like peak persists well above the MIR limit.
- -Maximal resistivity is an order of magnitude larger than $ho_{_{MIR}}$.



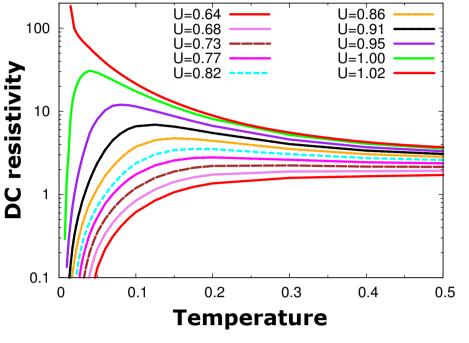


• Large scattering rate, $au^{-1}=-rac{1}{2}Im\Sigma(0^+)$, gives the main contribution to the resistivity temperature dependence, and causes the violation of the MIR condition. Above the MIR limit, $au^{-1}>E_F$, and therefore, well-defined quasi-particles do not exist. Similar conclusions are obtained from experiments on VO_2 [6], and κ -organics [7].



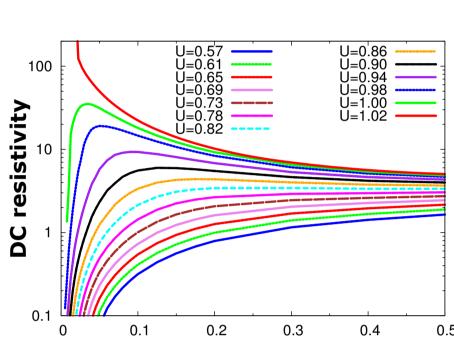
Effects of disorder

• **Disorder** effectively increases the bandwidth, and critical interaction U_c . Maximal value of ho_{DC} , and the critical temperature do not change appreciably with disorder.



Pure case

Uin units U_c^0



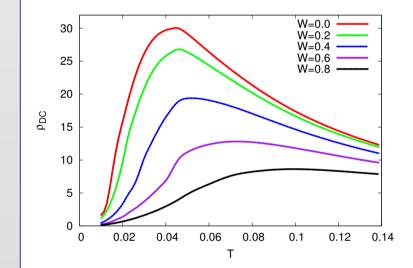
Temperature

Disordered case

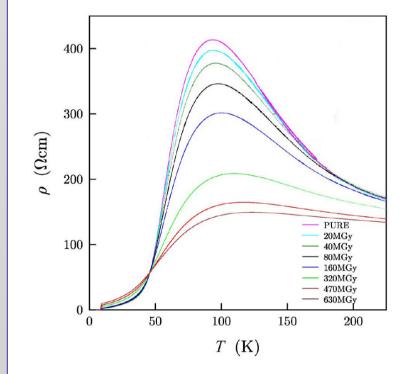
Uniformly distributed disorder in (-W/2, W/2), U in units $U_c(W)$.

Here $U_c^0 = 2.2$, W = 1, $U_c=2.45$. Increase in U_c with W agrees with earlier estimates [8].

Resistivity for fixed U

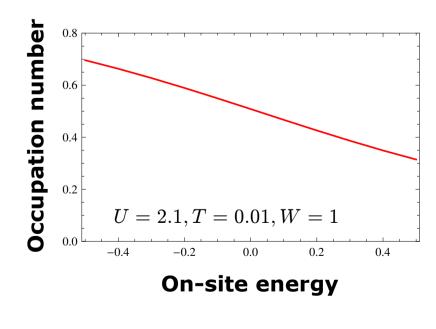


U is fixed to U_c^0 , disorder is varied



Experiments on X-ray irradiated κ -(BEDT-TTF)₂Cu(SCN)₂ [9]

 Effective local carrier doping disorder Random site energies change the local occupation number from half-filling, reducing the correlation effects and decreasing the resistivity. Similar physical picture is proposed as the explanation of the experiments on κ -organics [10].



ACKNOWLEDGEMENTS

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